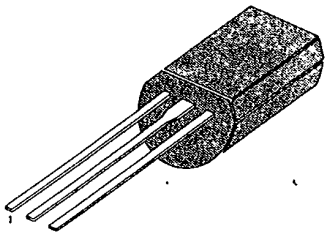
KSC2340 NPN EPITAXIAL SILICON TRANSISTOR

COLOR TV CHROMA OUTPUT

- Collector-Base Voltage V_{CBO}=350V
- Current Gain-Bandwidth Product f_T=50MHz (Typ)

TO-92L



1. Emitter 2. Collector 3. Base

ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	350	V
Collector-Emitter Voltage	V_{CEO}	350	V
Emitter-Base Voltage	V_{EBO}	7	V
Collector Current	I_C	100	mA
Collector Dissipation	P_C	1	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	−55 ~ 150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	I_C=100μA, I_E=0	350			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=5mA, I_B=0	350			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E=−100μA, I_C=0	7			V
Collector Cutoff Current	I_{CBO}	V_{CB}=200V, I_E=0			0.1	μA
DC Current Gain	h_{FE}	V_{CE}=10V, I_C=20mA	30		150	
Collector-Emitter Saturation Voltage	V_{CE} (sat)	I_C=10mA, I_B=1mA			0.5	V
Current Gain Bandwidth Product	f_T	V_{CE}=10V, I_C=20mA	50			MHz
Output Capacitance	Cob	V_{CB}=10V, I_E=0, f=1MHz		8		pF

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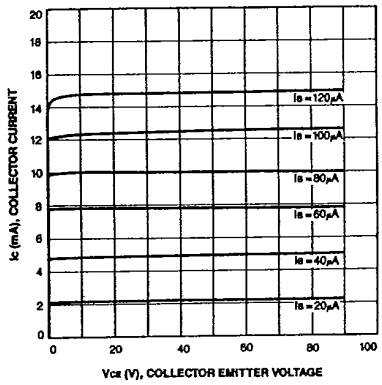
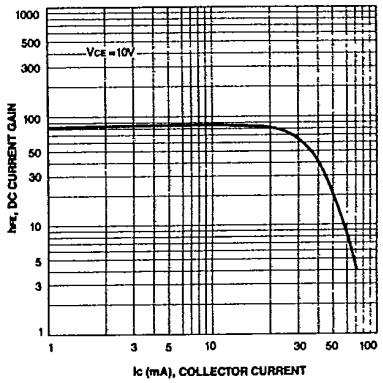
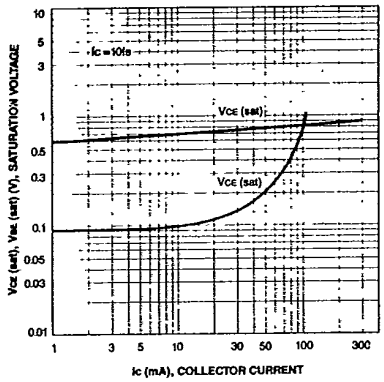
STATIC CHARACTERISTIC



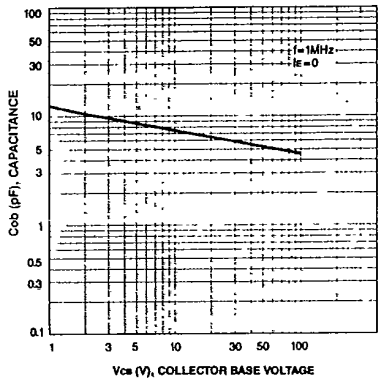
DC CURRENT GAIN



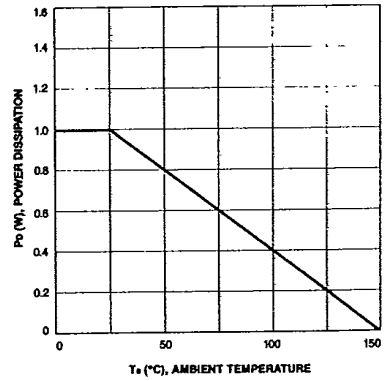
BASE-EMITTER SATURATION VOLTAGE
COLLECTOR-EMITTER SATURATION VOLTAGE



COLLECTOR OUTPUT CAPACITANCE



POWER DERATING



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